

## **isc Silicon PNP Power Transistor**

# 2SA1264N

### DESCRIPTION

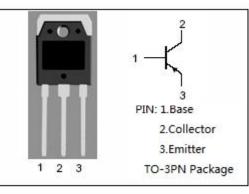
- Low Collector Saturation Voltage-
- : V<sub>CE(sat)</sub>= -2.0V(Min) @I<sub>C</sub>= -6A
- Good Linearity of  $h_{\text{FE}}$
- Complement to Type 2SC3181N
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

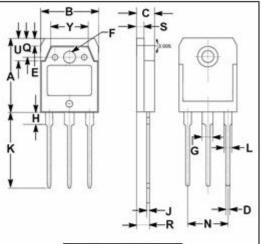
### APPLICATIONS

- Power amplifier applications
- Recommend for 55W high fidelity audio frequency amplifier output stage applications

### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-120	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-120	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current-Continuous	-8	A
IB	Base Current-Continuous	-0.8	A
Pc	Collector Power Dissipation @ $T_C=25^{\circ}C$	80	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C





	mm	
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
Κ	19.80	20.70
L	1.90	2.20
Ν	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

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## **ELECTRICAL CHARACTERISTICS**

#### $T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA; I <sub>B</sub> = 0	-120			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -6A; I <sub>B</sub> = -0.6A			-2.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -4A ; V <sub>CE</sub> = -5V			-1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -120V; I <sub>E</sub> = 0			-5	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-5	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -1A; V <sub>CE</sub> = -5V	55		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -4A; V <sub>CE</sub> = -5V	35			
Сов	Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -10V; f <sub>test</sub> = 1.0MHz		420		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> =-1A; V <sub>CE</sub> = -5V		30		MHz

#### h<sub>FE-1</sub> Classifications

R	ο	
55-110	80-160	

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